

DV 827C-800-50

Rectifier Diode

Properties

- low forward voltage drop
- low recovery charge
- high operating temperature
- low leakage current

Applications

- Rectifier bridges

Key Parameters

V_{RRM}	=	5 000	V
I_{FAVm}	=	1 028	A
I_{FSM}	=	12 000	A
V_{TO}	=	0.894	V
r_T	=	0.487	$\text{m}\Omega$

Types

	V_{RRM}
DV 827C-800-50	5 000 V
DV 827C-800-48	4 800 V
DV 827C-800-46	4 600 V
DV 827C-800-42	4 200 V
Conditions:	$T_j = -40 \div 160^\circ\text{C}$, half sine waveform, $f = 50\text{ Hz}$

Mechanical Data

F_m	Mounting force	$10 \pm 2 \text{ kN}$
m	Weight	0.20 kg
D_s	Surface creepage distance	20 mm
D_a	Air strike distance	14 mm

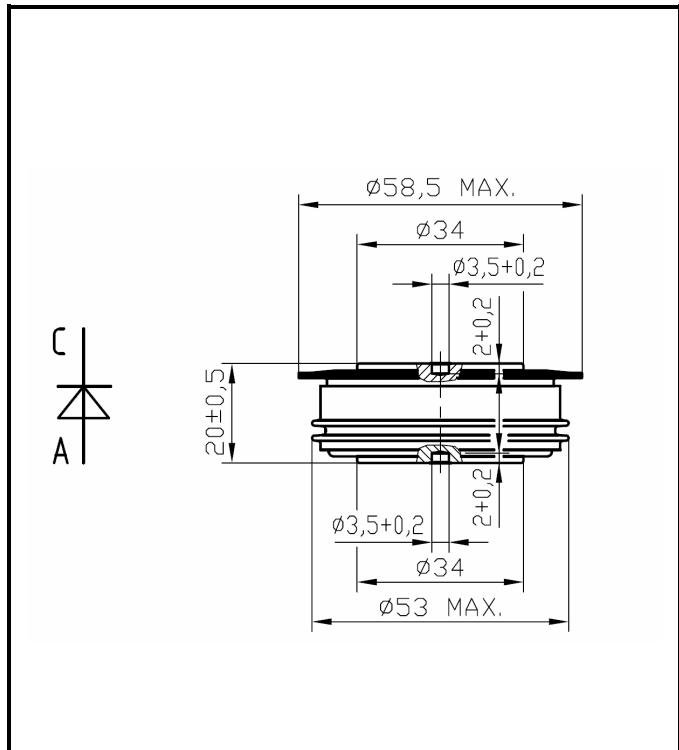


Fig. 1 Case

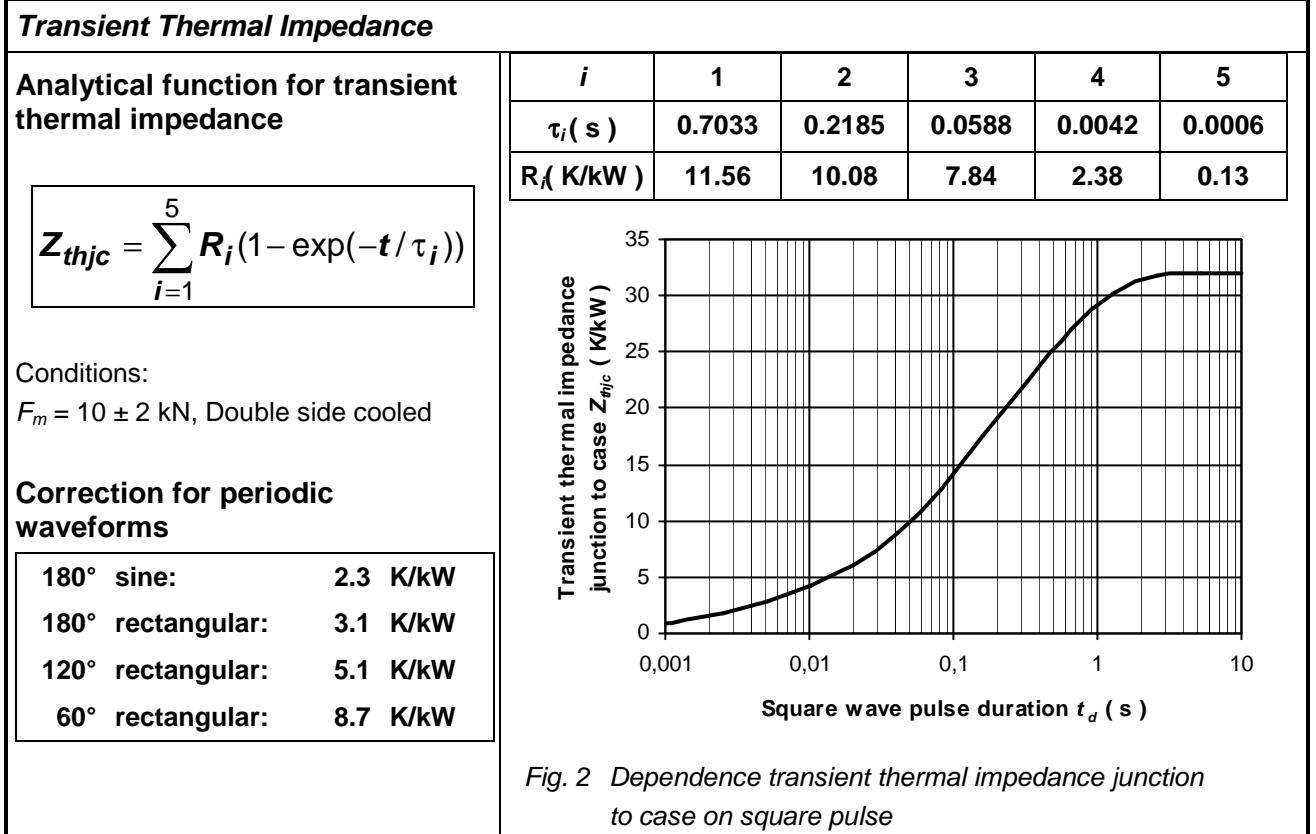
Maximum Ratings			Maximum Limits	Unit
V_{RRM}	Repetitive peak reverse voltage $T_j = -40 \div 160^\circ\text{C}$	DV 827C-800-50 DV 827C-800-48 DV 827C-800-46 DV 827C-800-42	5 000 4 800 4 600 4 200	V
I_{FAVm}	Average forward current $T_c = 85^\circ\text{C}$		1 028	A
I_{FRMS}	RMS forward current $T_c = 85^\circ\text{C}$		1 614	A
I_{RRM}	Repetitive reverse current $V_R = V_{RRM}$		30	mA
I_{FSM}	Non repetitive peak surge current $V_R = 0 \text{ V, half sine pulse, } T_j = 25^\circ\text{C}$	$t_p = 8.3 \text{ ms}$	16 000	A
		$t_p = 10 \text{ ms}$	15 000	A
	Non repetitive peak surge current $V_R = 0 \text{ V, half sine pulse}$	$t_p = 8.3 \text{ ms}$	12 800	A
		$t_p = 10 \text{ ms}$	12 000	A
$\int t$	Limiting load integral $V_R = 0 \text{ V, half sine pulse, } T_j = 25^\circ\text{C}$	$t_p = 8.3 \text{ ms}$	1 066 000	A^2s
		$t_p = 10 \text{ ms}$	1 125 000	A^2s
	Limiting load integral $V_R = 0 \text{ V, half sine pulse}$	$t_p = 8.3 \text{ ms}$	682 000	A^2s
		$t_p = 10 \text{ ms}$	720 000	A^2s
$T_{jmin} - T_{jmax}$	Operating temperature range		-40 \div 160	$^\circ\text{C}$
T_{STG}	Storage temperature range		-40 \div 160	$^\circ\text{C}$

Unless otherwise specified $T_j = 160^\circ\text{C}$

Characteristics		Value			Unit
		min	typ	max	
V_{To}	Threshold voltage			0.894	V
	Forward slope resistance $I_{F1} = 1 500 \text{ A, } I_{F2} = 4 500 \text{ A}$			0.487	$\text{m}\Omega$
V_{FM}	Maximum forward voltage $I_{FM} = 1 500 \text{ A}$			1.65	V
Q_{rr}	Recovered charge $V_R = 100 \text{ V, } I_{FM} = 1 000 \text{ A, } di/dt = -30 \text{ A}/\mu\text{s}$		2 400	3 500	μC

Unless otherwise specified $T_j = 160^\circ\text{C}$

Thermal Parameters			Value	Unit
R_{thjc}	Thermal resistance junction to case	<i>double side cooling</i>	32	K/kW
		<i>anode side cooling</i>	50	
		<i>cathode side cooling</i>	88	
R_{thch}	Thermal resistance case to heatsink	<i>double side cooling</i>	8	K/kW
		<i>single side cooling</i>	16	



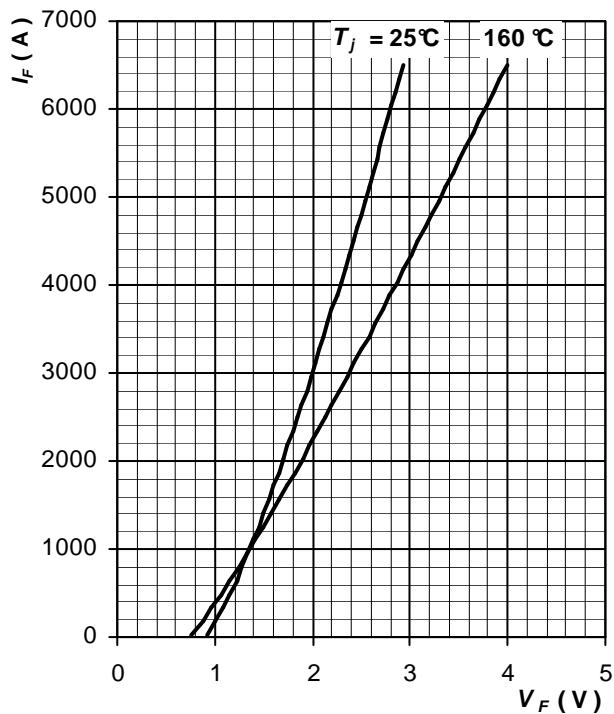


Fig. 3 Maximum forward voltage drop characteristics

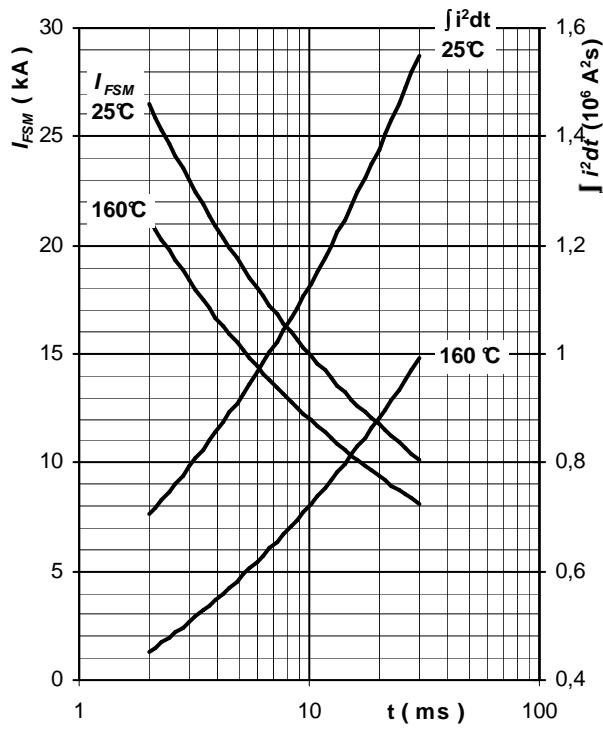


Fig. 4 Surge forward current vs. pulse length, half sine wave, single pulse, $V_R = 0 \text{ V}$

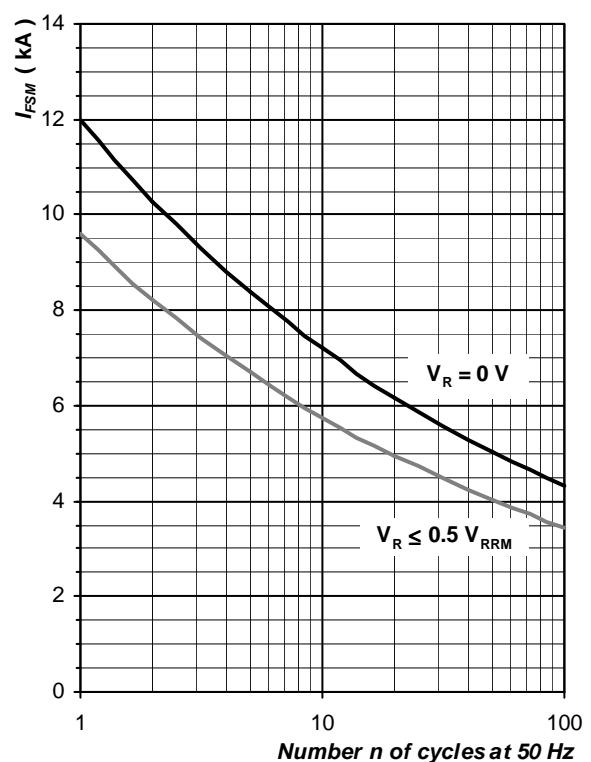


Fig. 5 Surge forward current vs. number of pulses, half sine wave, $T_j = T_{j\max}$

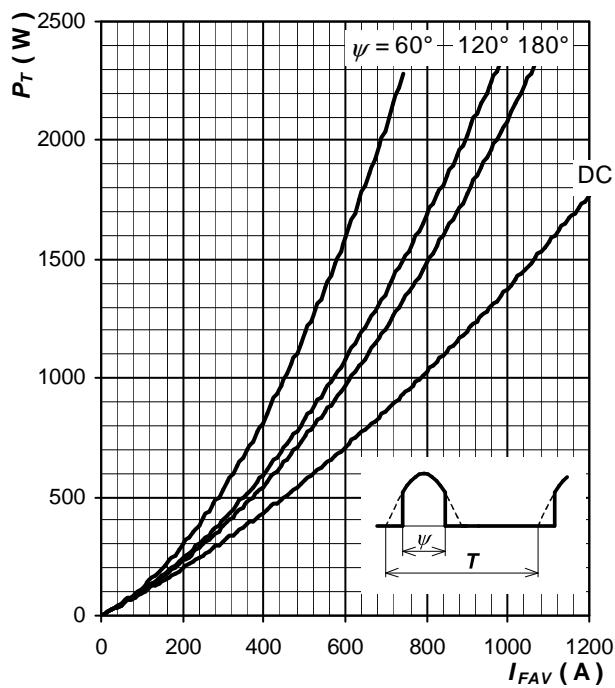


Fig. 6 Forward power loss vs. average forward current, sine waveform, $f = 50$ Hz, $T = 1/f$

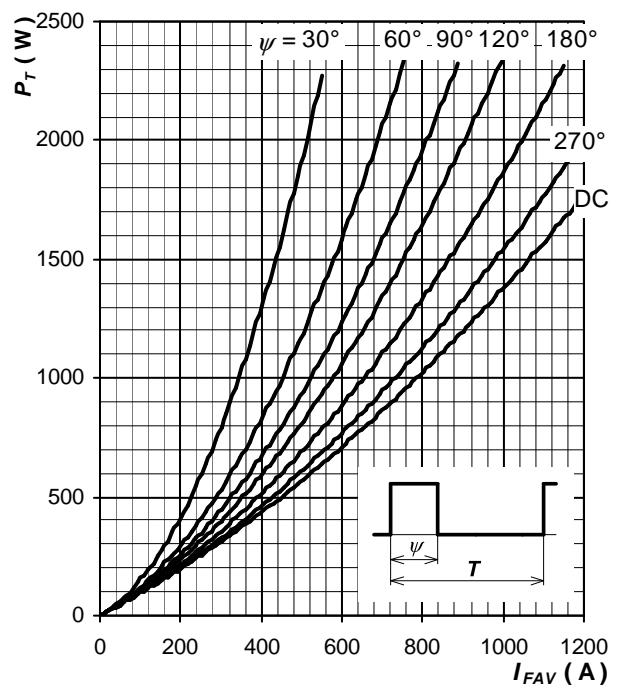


Fig. 7 Forward power loss vs. average forward current, square waveform, $f = 50$ Hz, $T = 1/f$

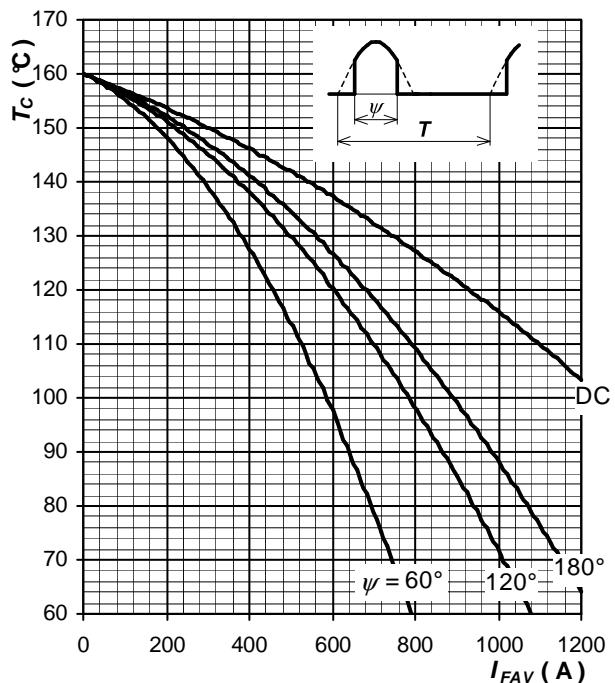


Fig. 8 Max. case temperature vs. aver. forward current, sine waveform, $f = 50$ Hz, $T = 1/f$

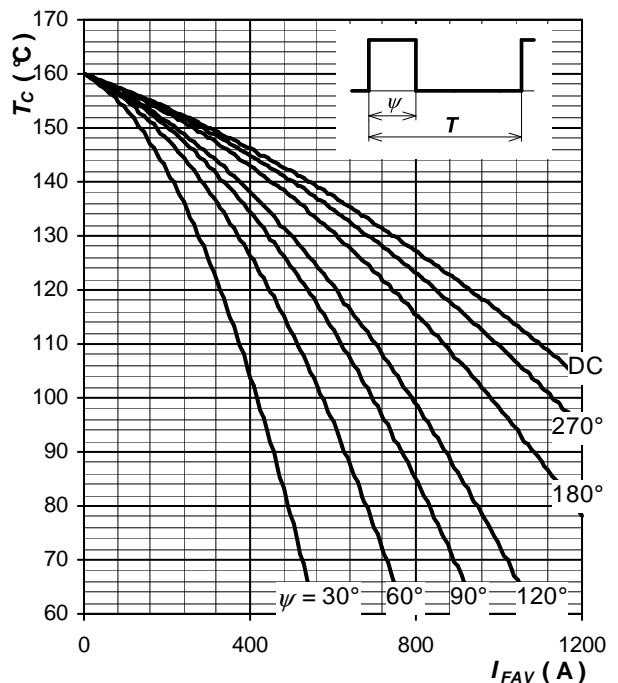


Fig. 9 Max. case temperature vs. aver. forward current, square waveform, $f = 50$ Hz, $T = 1/f$

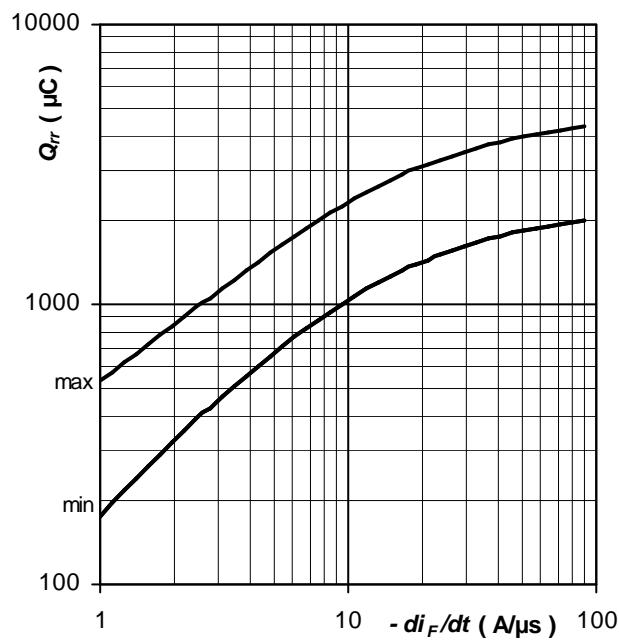


Fig. 10 Recovered charge Q_{rr}
vs. rate of fall forward current di_F/dt ,
trapezoid pulse, $I_{FM} = 1\,000\text{ A}$,
 $V_R = 100\text{ V}$, $T_j = T_{jmax}$

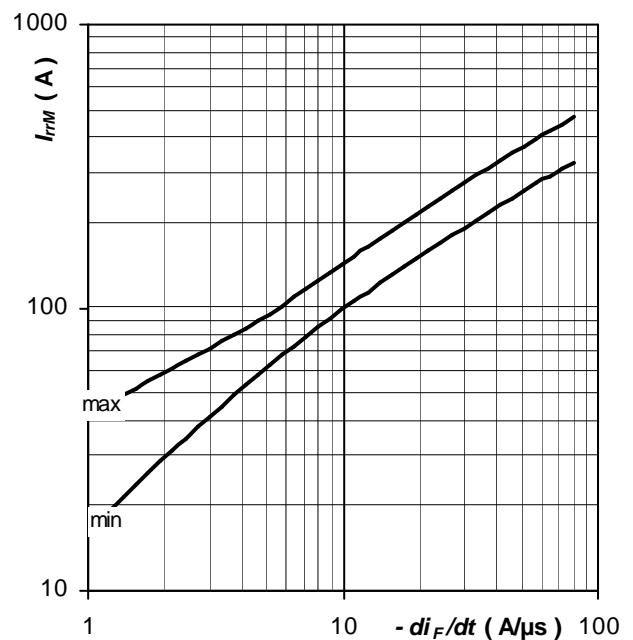


Fig. 11 Reverse recovery maximum current I_{rrM}
vs. rate of fall forward current di_F/dt ,
trapezoid pulse, $I_{FM} = 1\,000\text{ A}$,
 $V_R = 100\text{ V}$, $T_j = T_{jmax}$

Notes